

Final datasheet
CoolSiC™ 1200 V Schottky diode G5 with .XT interconnection technology

特性

- $V_{RRM} = 1200\text{ V}$ at $T_{vj} = 25^{\circ}\text{C}$
- $I_F = 40\text{ A}$
- No reverse recovery current / no forward recovery
- 高冲击电流能力
- Temperature independent switching behavior
- Low forward voltage
- dv/dt ruggedness
- Pb-free lead plating; RoHS compliant
- .XT interconnection technology for best-in-class thermal performance

可选应用

- String inverter
- Online UPS / Industrial UPS
- EV Charging
- Welding

产品认证

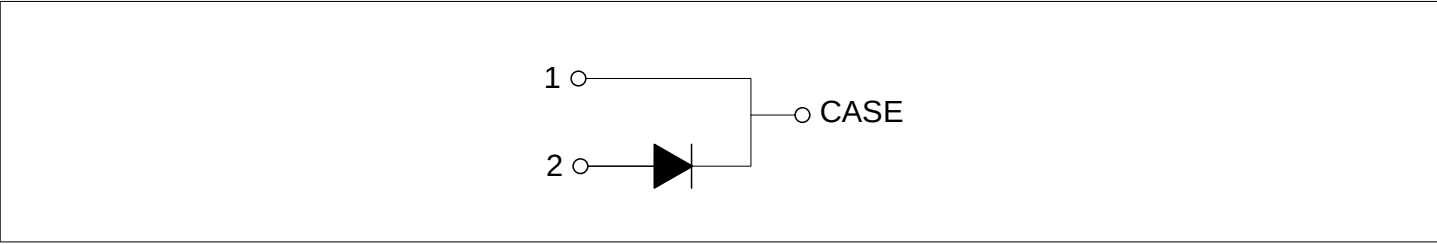
- Qualified for industrial applications according to the relevant tests of JEDEC47/20/22

描述

Pin definition:

Pin 1 & backside – Cathode

Pin 2 – Anode



Type	Package	Marking
IDWD40G120C5	PG-TO247-2-U01	D4012C5



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1 封装

1 封装

表 1 特征值

特征参数	代号	标注或测试条件	数值			单位
			最小值	典型值	最大值	
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature	T_{sold}	wave soldering 1.6 mm (0.063 in.) from case for 10 s			260	°C
Mounting torque	M	M3 screw, Maximum of mounting processes: 3			0.6	Nm
Thermal resistance, junction-ambient	$R_{\text{th(j-a)}}$				62	K/W
Diode thermal resistance, junction-case	$R_{\text{th(j-c)}}$			0.27	0.35	K/W

2 SiC Diode

表 2 最大标定值

特征参数	代号	标注或测试条件		数值	单位
Repetitive peak reverse voltage	V_{RRM}	$T_{\text{vj}} \geq 25\text{ °C}$		1200	V
Continuous forward current for $R_{\text{th(j-c,max)}}$	I_{F}		$T_{\text{c}} = 25\text{ °C}$	109	A
			$T_{\text{c}} = 135\text{ °C}$	50	
			$T_{\text{c}} = 147\text{ °C}$	40	
Surge repetitive forward current, sine halfwave ¹⁾	$I_{\text{F,RM}}$	$t_{\text{p}} = 10\text{ ms}$	$T_{\text{c}} = 25\text{ °C}$	160	A
			$T_{\text{c}} = 100\text{ °C}$	120	
Surge non-repetitive forward current, sine halfwave	$I_{\text{F,SM}}$	$t_{\text{p}} = 10\text{ ms}$	$T_{\text{c}} = 25\text{ °C}$	290	A
			$T_{\text{c}} = 150\text{ °C}$	280	
Non-repetitive peak forward current	$I_{\text{F,max}}$	$T_{\text{c}} = 25\text{ °C}, t_{\text{p}} = 10\text{ }\mu\text{s}$		1588	A
I^2t value	$\int I^2t$	$t_{\text{p}} = 10\text{ ms}$ ²⁾	$T_{\text{c}} = 25\text{ °C}$	420	A ² s
			$T_{\text{c}} = 150\text{ °C}$	392	
Diode dv/dt ruggedness	dv/dt	$V_{\text{R}} = 0\text{...}960\text{ V}$		150	V/ns
Avalanche energy, single pulse	E_{AS}	$I_{\text{D}} = 35\text{ A}, V_{\text{DD}} = 50\text{ V}, L = 0.5\text{ mH}$		299	mJ
Power dissipation for $R_{\text{th(j-c,max)}}$	P_{tot}		$T_{\text{c}} = 25\text{ °C}$	428	W
			$T_{\text{c}} = 100\text{ °C}$	214	

1) Not subject to production test. The test was performed with 20k pulses (half-wave rectified sine with 10 ms period).

2) sine halfwave

表 3 **特征值**

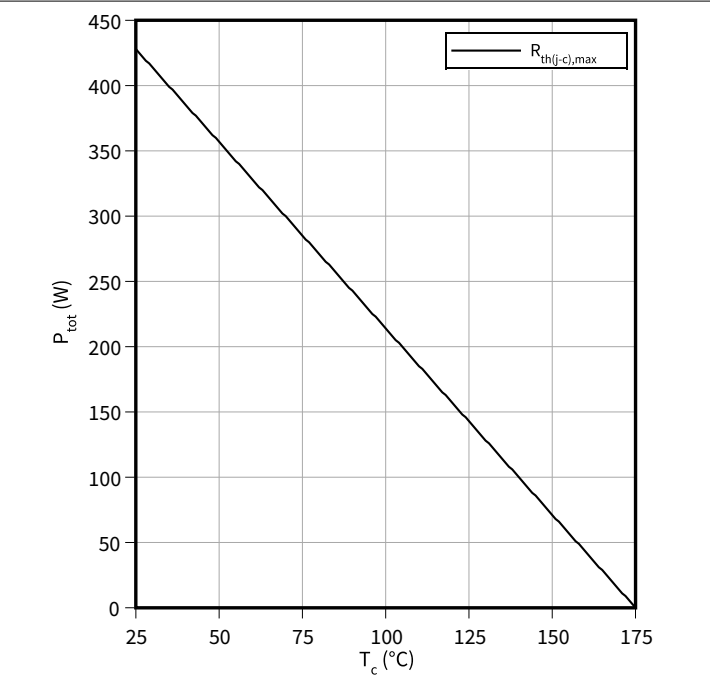
特征参数	代号	标注或测试条件		数值			单位
				最小值	典型值	最大值	
DC blocking voltage	V_{DC}	$I_R = 500 \mu A, T_{vj} = 25^\circ C$		1200			V
Diode forward voltage	V_F	$I_F = 40 A$	$T_{vj} = 25^\circ C$		1.45	1.8	V
			$T_{vj} = 125^\circ C$		1.69		
			$T_{vj} = 150^\circ C$		1.8		
Reverse current	I_R	$V_R = 1200 V$	$T_{vj} = 25^\circ C$		20	320	μA
			$T_{vj} = 150^\circ C$		105		
Total capacitive charge	Q_C	$V_R = 800 V, T_{vj} = 25^\circ C \text{ \& } 150^\circ C,$ $Q_C = \int_0^{V_R} C(V)dV$			182		nC
Total capacitance	C	$f = 100 \text{ kHz}$	$V_R = 1 V$		2350		pF
			$V_R = 400 V$		166		
			$V_R = 800 V$		130		
Operating junction temperature	T_{vj}			-55		175	$^\circ C$

注: *For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.*
Electrical Characteristic, at $T_{vj} = 25^\circ C$, unless otherwise specified.

3 特征参数图表

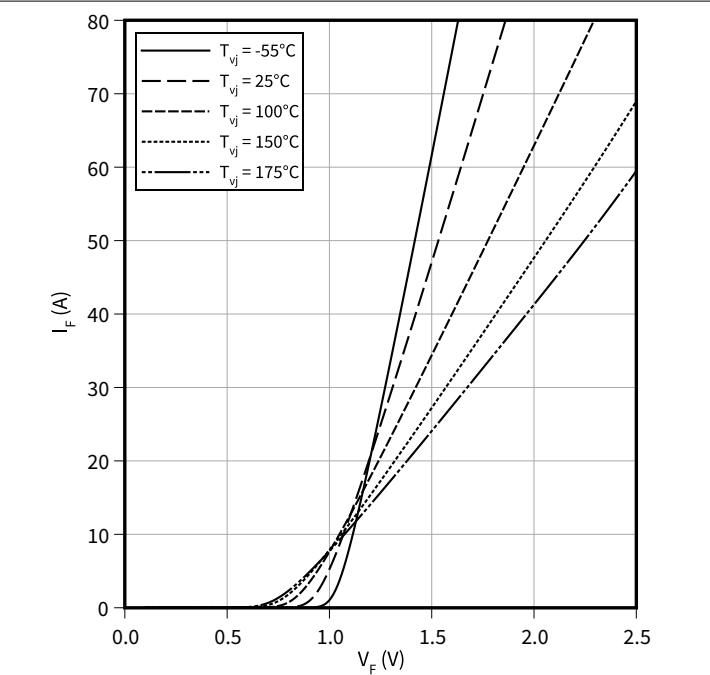
Power dissipation as function of case temperature

$P_{\text{tot}} = f(T_c)$
 $T_{vj} \leq 175\text{ }^{\circ}\text{C}$



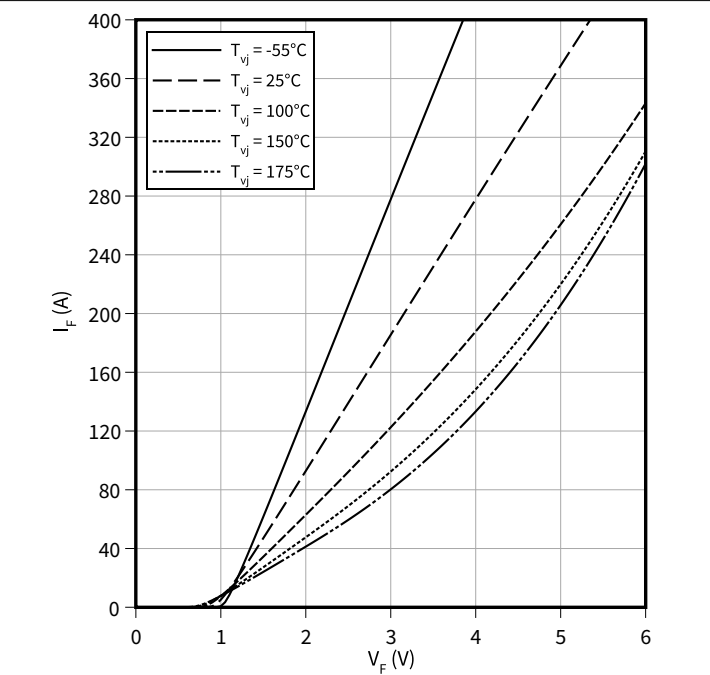
Typical forward characteristics

$I_F = f(V_F)$
 $t_p = 10\text{ }\mu\text{s}$



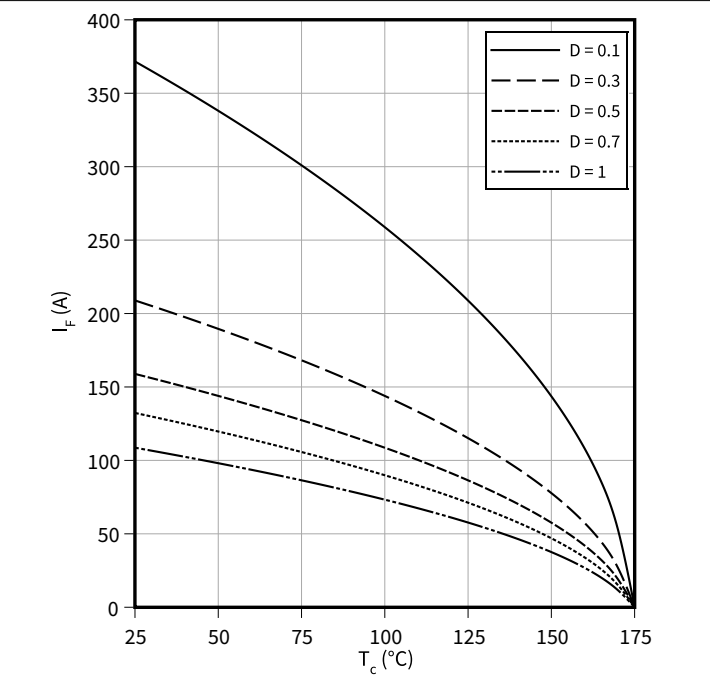
Typical forward characteristics in surge current

$I_F = f(V_F)$
 $t_p = 10\text{ }\mu\text{s}$



Diode forward current as function of temperature

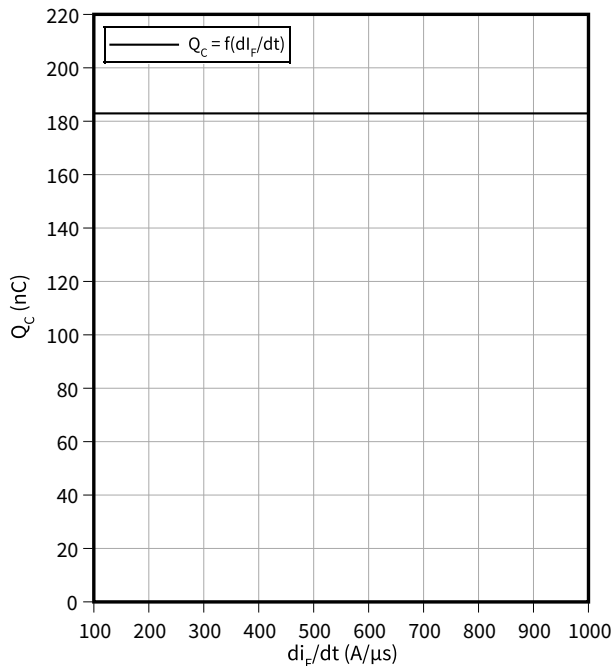
$I_F = f(T_c)$
 $T_{vj} \leq 175\text{ }^{\circ}\text{C}$



3 特征参数图表

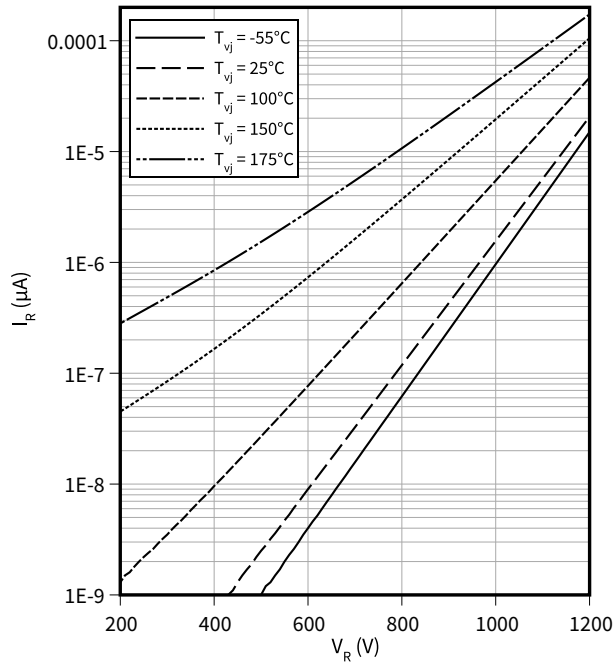
Typical capacitive charge as function of current slope

$Q_C = f(di_F/dt)$
 $T_{vj} = 25\text{ }^{\circ}\text{C}, V_R = 800\text{ V}$



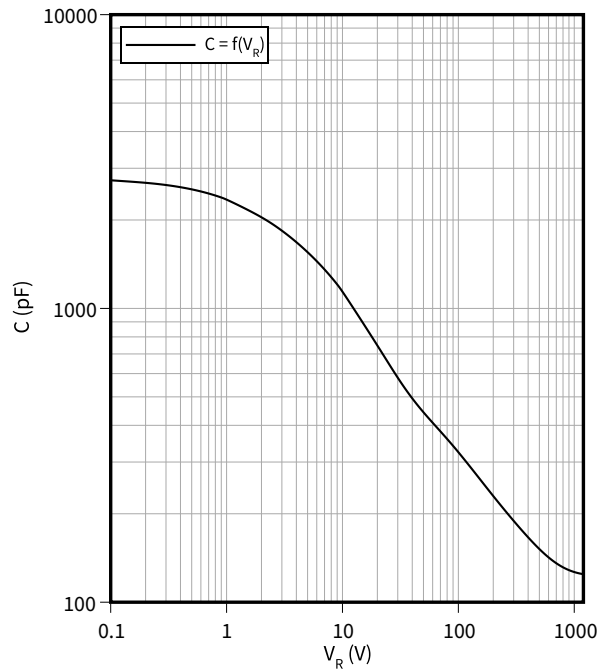
Typical reverse characteristics

$I_R = f(V_R)$



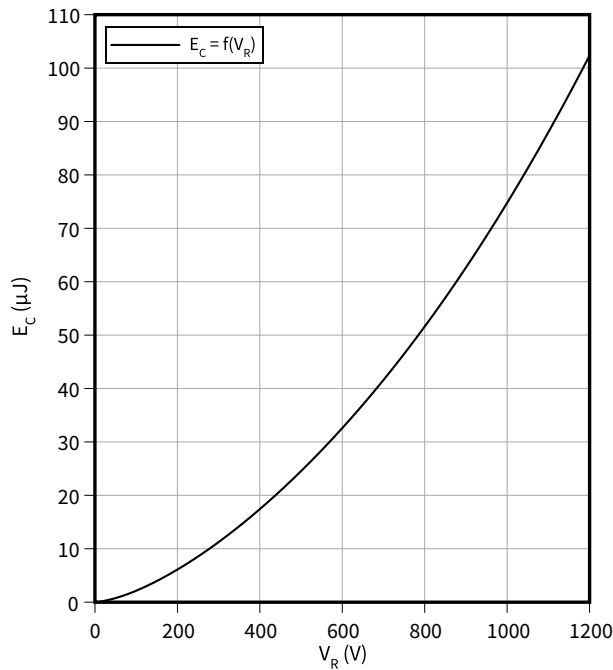
Typical capacitance as function of reverse voltage

$C = f(V_R)$
 $T_{vj} = 25\text{ }^{\circ}\text{C}, f = 100\text{ kHz}$



Typical capacitively stored energy as function of reverse voltage

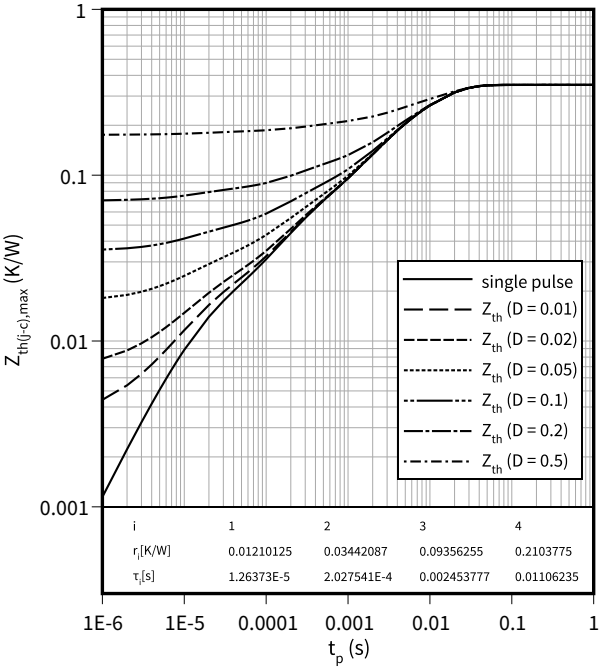
$E_C = f(V_R)$



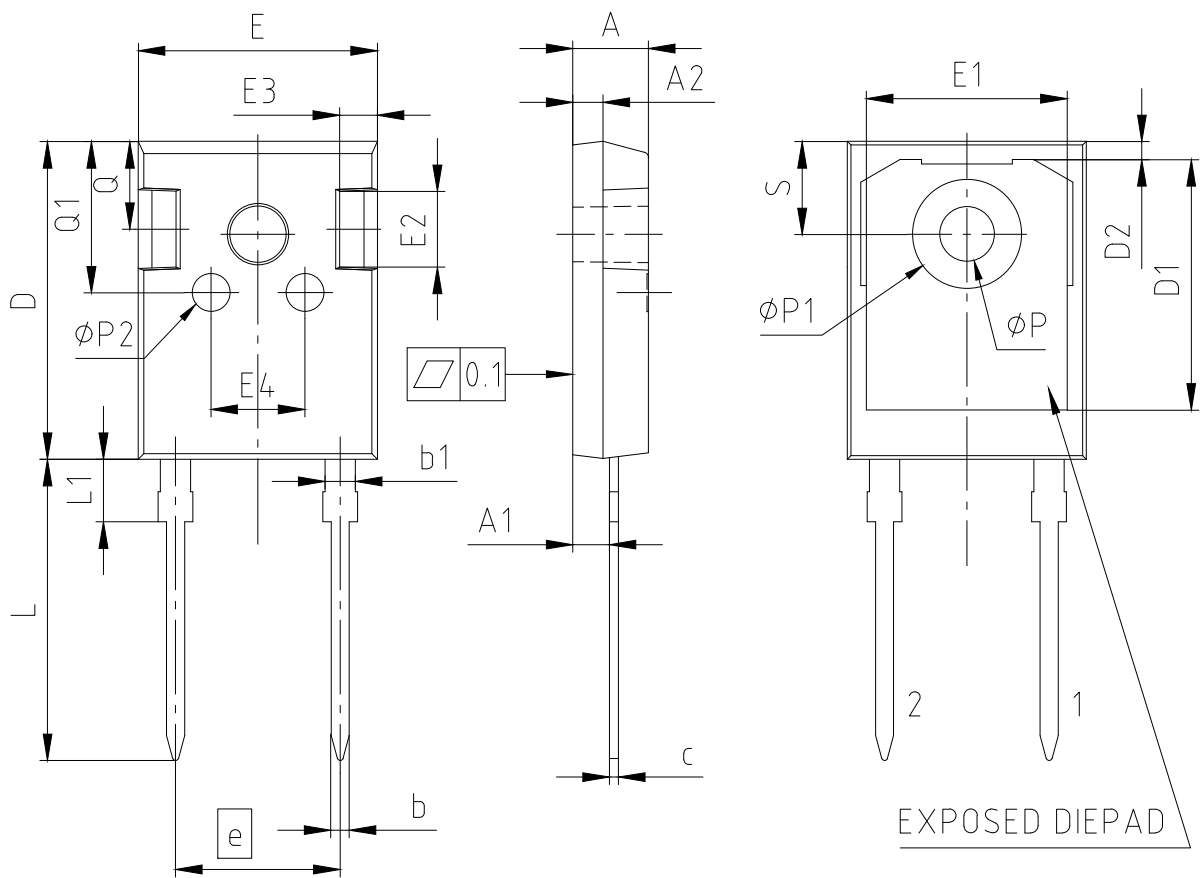
3 特征参数图表

Max. transient thermal impedance

$Z_{th(j-c),max} = f(t_p)$
 $D = t_p/T$



4 封装尺寸



PACKAGE - GROUP NUMBER:		PG-T0247-2-U01			
DIMENSIONS	MILLIMETERS				
	MIN.	MAX.			
A	4.90	5.10	L	19.80	20.10
A1	2.31	2.51	L1	---	4.30
A2	1.90	2.10	ØP	3.50	3.70
b	1.16	1.26	ØP1	7.00	7.40
b1	1.96	2.06	ØP2	2.40	2.60
c	0.59	0.66	Q	5.60	6.00
D	20.90	21.10	Q1	9.80	10.20
D1	16.25	16.85	S	6.05	6.25
D2	1.05	1.35			
E	15.70	15.90			
E1	13.10	13.50			
E2	4.90	5.10			
E3	2.40	2.60			
E4	6.00	6.40			
e	10.88				
N	2				

ALL DIMENSIONS DO NOT INCLUDE
MOLD FLASH OR PROTRUSIONS.

图 1



修订历史

修订历史

修订版本	发布日期	变更说明
0.10	2023-08-02	Target datasheet
0.20	2024-10-16	Preliminary datasheet
1.00	2025-01-14	Final datasheet

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